WHAT IS CLAIMED IS:

1. A wiring board wherein an opening is defined at a predetermined position of a film-like insulating substrate, an electric wiring provided with a connection terminal covering the opening is disposed on a principal plane of the insulating substrate, and a conductive member to be connected with the connection terminal of the electric wiring is disposed inside the opening, comprising:

said conductive member having a thickness from a surface on which said electric wiring of the insulating substrate has been disposed being thinner than that of said insulating substrate.

2. A wiring board as claimed in claim 2, wherein:

a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

3. A wiring board as claimed in claim 1, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

4. A wiring board as claimed in claim 2, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

5. A wiring board as claimed in claim 1, wherein:

said conductive member is made from any member selected from

the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

6. A wiring board as claimed in claim 2, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

7. A wiring board as claimed in claim 3, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

8. A wiring board as claimed in claim 1, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

9. A wiring board as claimed in claim 2, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

10. A wiring board as claimed in claim 3, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

11. A wiring board as claimed in claim 4, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said

conductive member.

12. A semiconductor device wherein a wiring board in which an opening is defined at a predetermined position of a film-like insulating substrate, an electric wiring provided with a connection terminal covering said opening is disposed on a principal plane of said insulating substrate, and a conductive member to be connected with the connection terminal of said electric wiring is disposed inside the opening is placed; a semiconductor chip is placed on the surface of said wiring board on which said electric wiring has been disposed; the electric wiring of said wiring board is electrically connected with an external electrode of the semiconductor chip; and said semiconductor chip, said electric wiring, and connecting section for said electric wiring and said external electrode of the semiconductor chip are sealed with a sealing insulator, comprising:

said conductive member having a thickness from a surface on which said electric wiring of the insulating substrate has been formed being thinner than that of said insulating substrate.

13. A semiconductor device as claimed in claim 12, wherein:

said semiconductor chip is placed in such that a surface opposed to the surface on which said external electrode has been formed is opposed to said wiring board; and

said external electrode is connected with said electric wiring by means of a bonding wire.

14. A semiconductor device as claimed in claim 12, wherein:

said semiconductor chip is placed in such that said external electrode thereof is opposed to said wiring board; and

said external electrode is connected with said electric wiring by means of a protrusion conductor.

15. A semiconductor device as claimed in claim 8, wherein:

a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

16. A semiconductor device as claimed in claim 12, wherein:

a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

17. A semiconductor device as claimed in claim 13, wherein:

a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

18. A semiconductor device as claimed in claim 14, wherein:

a thickness of said conductive member is 1/2 or more of that of said insulating substrate.

19. A semiconductor device as claimed in claim 8, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

20. A semiconductor device as claimed in claim 12, wherein:

said conductive member has a thinner thickness at the central

portion of said opening than that of a vicinity of a side wall of said opening.

21. A semiconductor device as claimed in claim 13, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

22. A semiconductor device as claimed in claim 14, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

23. A semiconductor device as claimed in claim 15, wherein:

said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

24. A semiconductor device as claimed in claim 8, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

25. A semiconductor device as claimed in claim 12, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

26. A semiconductor device as claimed in claim 13, wherein:

said conductive member is made from any member selected from

the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

27. A semiconductor device as claimed in claim 14, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

28. A semiconductor device as claimed in claim 15, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

29. A semiconductor device as claimed in claim 19, wherein:

said conductive member is made from any member selected from the group consisting of copper (Cu), nickel (Ni), and silver (Ag).

30. A semiconductor device as claimed in claim 8, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

31. A semiconductor device as claimed in claim 12, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

32. A semiconductor device as claimed in claim 13, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

33. A semiconductor device as claimed in claim 14, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

34. A semiconductor device as claimed in claim 15, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

35. A semiconductor device as claimed in claim 19, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

36. A semiconductor device as claimed in claim 24, wherein:

a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) are sequentially disposed on a surface of said conductive member.

37. A process for the production of a wiring board, comprising the steps of:

defining an opening at a predetermined position of a film-like insulating substrate;

forming a conductive thin film on a principal plane of said insulating substrate;

etching said conductive thin film to form an electric wiring

provided with a connection terminal covering said opening; and

forming a conductive member having a thickness equal to or thinner than that of said insulating substrate.

38. A process for the production of a wiring board, comprising the steps of:

defining an opening at a predetermined position of a film-like insulating substrate;

forming a conductive thin film on a principal plane of said insulating substrate;

etching said conductive thin film to form an electric wiring provided with a connection terminal covering said opening;

forming a conductive member having a thickness equal to or thinner than that of said insulating substrate; and

forming sequentially a thin film layer made of nickel (Ni) and a thin film layer made of gold (Au) on the surfaces of said electric wiring and said conductive member.

39 ~~40~~. A process for the production of a wiring board as claimed in claim 37, wherein:

a step for forming said conductive member is effected by forming a copper (Cu) plating or a nickel (Ni) plating in accordance with electroplating method.

40 ~~41~~. A process for the production of a wiring board as claimed in claim 38, wherein:

a step for forming said conductive member is effected by forming a copper (Cu) plating or a nickel (Ni) plating in accordance with

electroplating method.

42. A process for the production of a wiring board as claimed in claim 37, wherein:

a step for forming said conductive member is effected by forming a nickel (Ni) plating in accordance with electroless plating method.

43. A process for the production of a wiring board as claimed in claim 38, wherein:

a step for forming said conductive member is effected by forming a nickel (Ni) plating in accordance with electroless plating method.

43. A process for the production of a wiring board as claimed in claim 37, wherein:

a step for forming said conductive member is effected by such a manner that the inside of said opening is filled with a conductive paste of silver (Ag) or copper (Cu), and said conductive paste is solidified.

44. A process for the production of a wiring board as claimed in claim 38, wherein:

a step for forming said conductive member is effected by such a manner that the inside of said opening is filled with a conductive paste of silver (Ag) or copper (Cu), and said conductive paste is solidified.

45. A process for the production of a wiring board as claimed in claim 37, wherein:

a step for forming said conductive member is effected by such a manner that said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

46. A process for the production of a wiring board as claimed in claim 38, wherein:

a step for forming said conductive member is effected by such a manner that said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

47. A process for the production of a wiring board as claimed in claim 39, wherein:

a step for forming said conductive member is effected by such a manner that said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

48. A process for the production of a wiring board as claimed in claim 41, wherein:

a step for forming said conductive member is effected by such a manner that said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.

49. A process for the production of a wiring board as claimed in claim 43, wherein:

a step for forming said conductive member is effected by such a manner that said conductive member has a thinner thickness at the central portion of said opening than that of a vicinity of a side wall of said opening.